



## N-Channel 100-V (D-S) MOSFET

## PRODUCT SUMMARY

| $V_{DS}$ (V) | $r_{DS(on)}$ ( $\Omega$ ) | $I_D$ (A) |
|--------------|---------------------------|-----------|
| 100          | 0.062 @ $V_{GS} = 10$ V   | 5.4       |
|              | 0.084 @ $V_{GS} = 6$ V    | 4.6       |

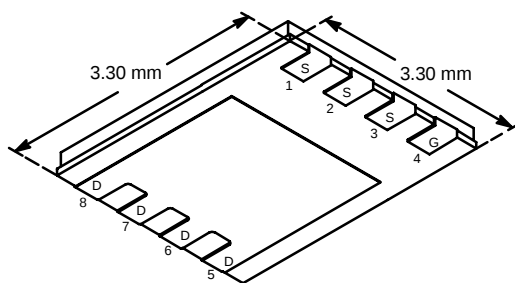
## FEATURES

- TrenchFET® Power MOSFET
- New Low Thermal Resistance
- PowerPAK™ 1212-8 Package with Low 1.07-mm-Profile
- PWM Optimized

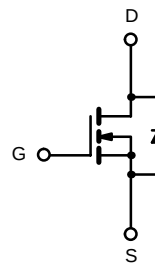
## APPLICATIONS

- Primary Side Switch
- In-Rush Current Limiter

PowerPAK™ 1212-8



Bottom View



N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS ( $T_A = 25^\circ\text{C}$  UNLESS OTHERWISE NOTED)

| Parameter                                                      |                       | Symbol                            | 10 secs    | Steady State | Unit |
|----------------------------------------------------------------|-----------------------|-----------------------------------|------------|--------------|------|
| Drain-Source Voltage                                           |                       | V <sub>DS</sub>                   | 100        |              | V    |
| Gate-Source Voltage                                            |                       | V <sub>GS</sub>                   | ± 20       |              |      |
| Continuous Drain Current (T <sub>J</sub> = 150°C) <sup>a</sup> | T <sub>A</sub> = 25°C | I <sub>D</sub>                    | 5.4        | 3.4          | A    |
|                                                                | T <sub>A</sub> = 70°C |                                   | 4.3        | 2.8          |      |
| Pulsed Drain Current                                           |                       | I <sub>DM</sub>                   | 20         |              |      |
| Continuous Source Current (Diode Conduction) <sup>a</sup>      |                       | I <sub>S</sub>                    | 3.2        | 1.3          |      |
| Single Avalanche Current                                       | L = 0.1 mH            | I <sub>AS</sub>                   | 19         |              | mJ   |
| Single Avalanche Energy                                        |                       | E <sub>AS</sub>                   | 18         |              |      |
| Maximum Power Dissipation <sup>a</sup>                         | T <sub>A</sub> = 25°C | P <sub>D</sub>                    | 3.8        | 1.5          | W    |
|                                                                | T <sub>A</sub> = 70°C |                                   | 2.0        | 0.8          |      |
| Operating Junction and Storage Temperature Range               |                       | T <sub>J</sub> , T <sub>stg</sub> | -55 to 150 |              | °C   |

## THERMAL RESISTANCE RATINGS

| Parameter                                |                 | Symbol     | Typical | Maximum | Unit               |
|------------------------------------------|-----------------|------------|---------|---------|--------------------|
| Maximum Junction-to-Ambient <sup>a</sup> | $t \leq 10$ sec | $R_{thJA}$ | 26      | 33      | $^\circ\text{C/W}$ |
|                                          | Steady State    |            | 65      | 81      |                    |
| Maximum Junction-to-Case (Drain)         | Steady State    | $R_{thJC}$ | 1.9     | 2.4     |                    |

Notes

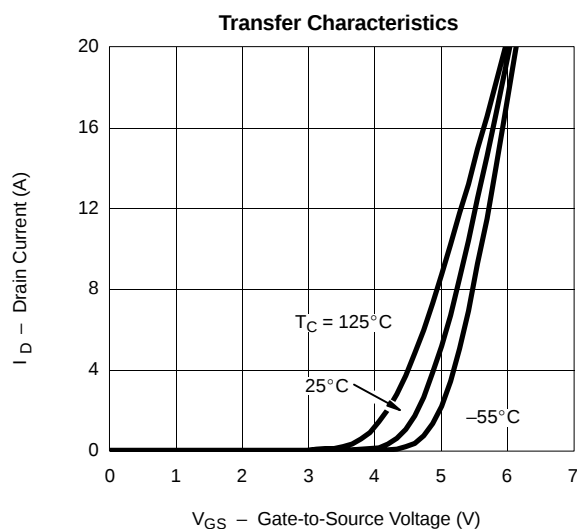
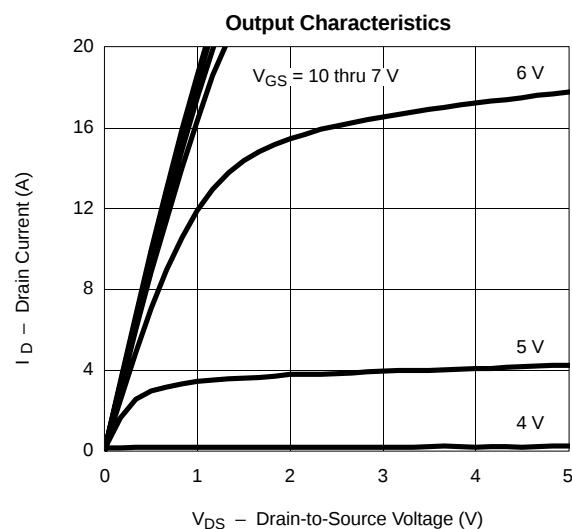
a. Surface Mounted on 1" x 1" FR4 Board.

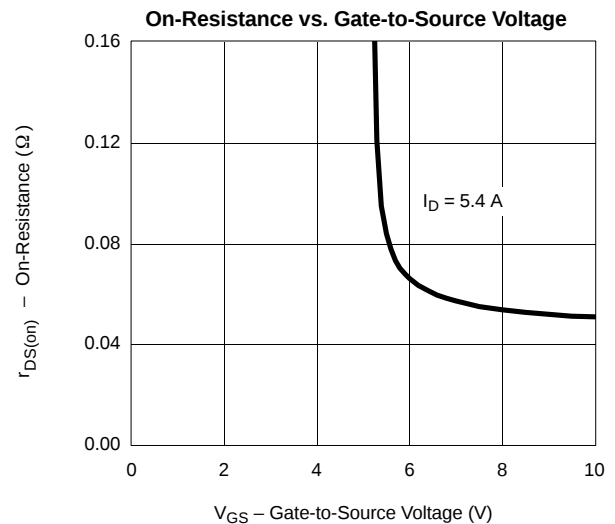
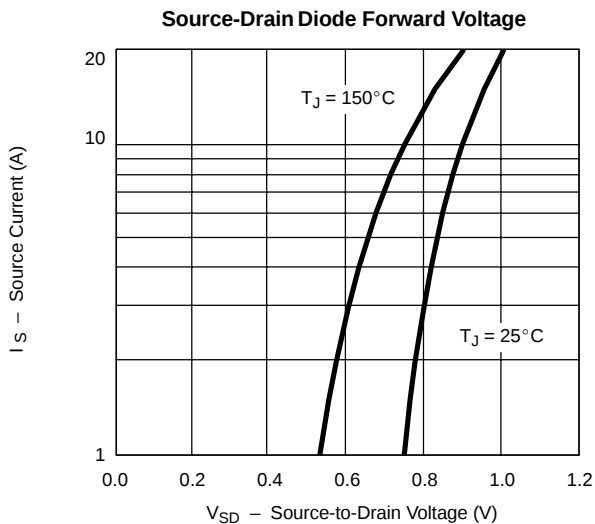
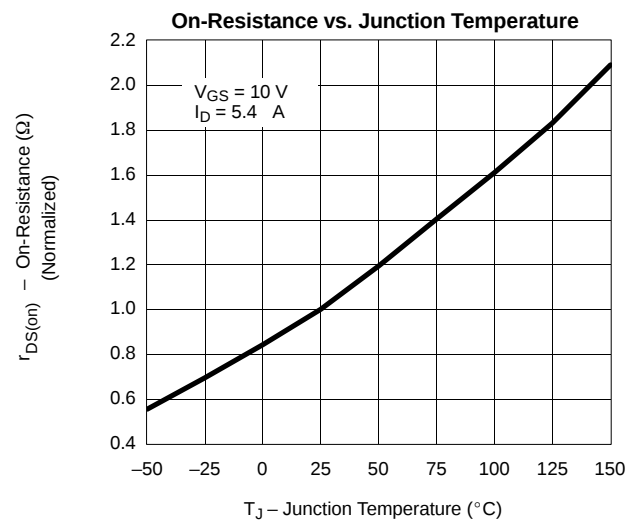
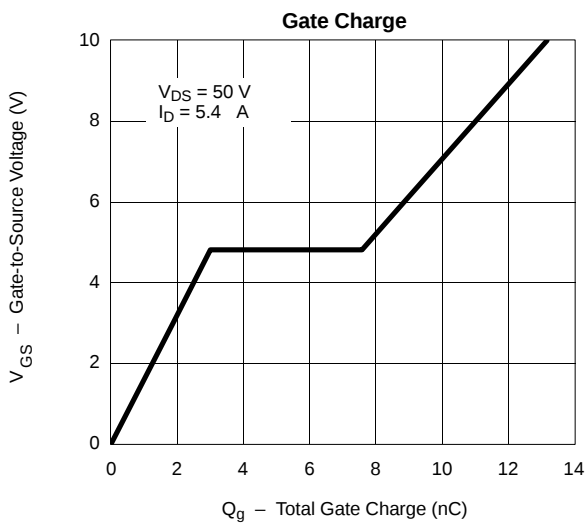
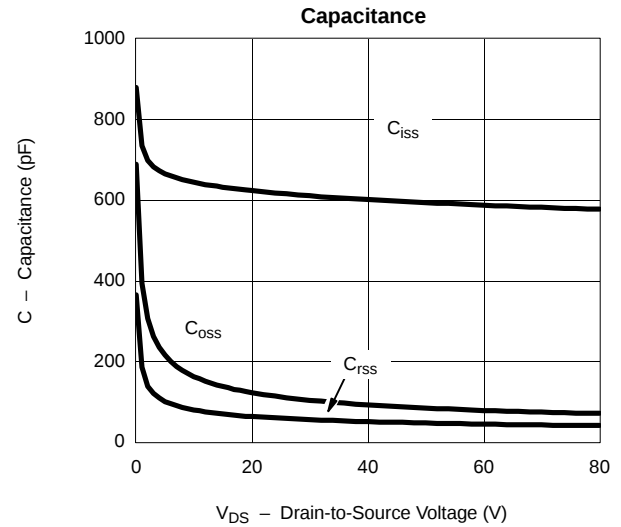
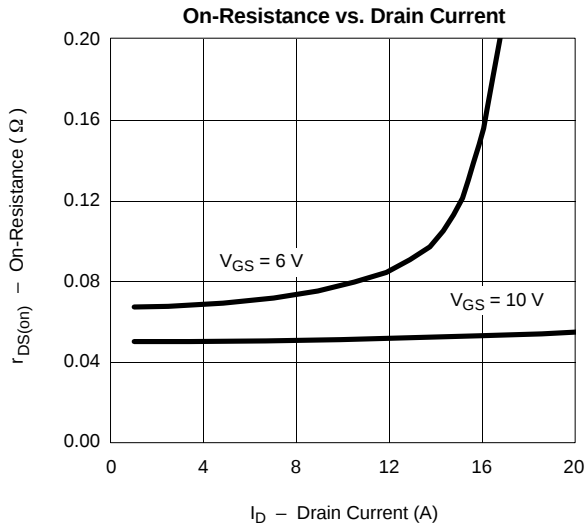
**MOSFET SPECIFICATIONS ( $T_J = 25^\circ\text{C}$  UNLESS OTHERWISE NOTED)**

| Parameter                                     | Symbol       | Test Condition                                                                                                         | Min | Typ   | Max       | Unit          |
|-----------------------------------------------|--------------|------------------------------------------------------------------------------------------------------------------------|-----|-------|-----------|---------------|
| <b>Static</b>                                 |              |                                                                                                                        |     |       |           |               |
| Gate Threshold Voltage                        | $V_{GS(th)}$ | $V_{DS} = V_{GS}$ , $I_D = 250\ \mu\text{A}$                                                                           | 2   |       |           | V             |
| Gate-Body Leakage                             | $I_{GSS}$    | $V_{DS} = 0\ \text{V}$ , $V_{GS} = \pm 20\ \text{V}$                                                                   |     |       | $\pm 100$ | nA            |
| Zero Gate Voltage Drain Current               | $I_{DSS}$    | $V_{DS} = 80\ \text{V}$ , $V_{GS} = 0\ \text{V}$                                                                       |     |       | 1         | $\mu\text{A}$ |
|                                               |              | $V_{DS} = 80\ \text{V}$ , $V_{GS} = 0\ \text{V}$ , $T_J = 55^\circ\text{C}$                                            |     |       | 5         |               |
| On-State Drain Current <sup>a</sup>           | $I_{D(on)}$  | $V_{DS} \geq 5\ \text{V}$ , $V_{GS} = 10\ \text{V}$                                                                    | 20  |       |           | A             |
| Drain-Source On-State Resistance <sup>a</sup> | $r_{DS(on)}$ | $V_{GS} = 10\ \text{V}$ , $I_D = 5.4\ \text{A}$                                                                        |     | 0.052 | 0.062     | $\Omega$      |
|                                               |              | $V_{GS} = 6\ \text{V}$ , $I_D = 4.6\ \text{A}$                                                                         |     | 0.070 | 0.084     |               |
| Forward Transconductance <sup>a</sup>         | $g_{fs}$     | $V_{DS} = 15\ \text{V}$ , $I_D = 5.4\ \text{A}$                                                                        |     | 12    |           | S             |
| Diode Forward Voltage <sup>a</sup>            | $V_{SD}$     | $I_S = 3.2\ \text{A}$ , $V_{GS} = 0\ \text{V}$                                                                         |     | 0.78  | 1.2       | V             |
| <b>Dynamic<sup>b</sup></b>                    |              |                                                                                                                        |     |       |           |               |
| Total Gate Charge                             | $Q_g$        | $V_{DS} = 50\ \text{V}$ , $V_{GS} = 10\ \text{V}$ , $I_D = 5.4\ \text{A}$                                              |     | 13.5  | 17        | nC            |
| Gate-Source Charge                            | $Q_{gs}$     |                                                                                                                        |     | 3     |           |               |
| Gate-Drain Charge                             | $Q_{gd}$     |                                                                                                                        |     | 4.6   |           |               |
| Turn-On Delay Time                            | $t_{d(on)}$  | $V_{DD} = 50\ \text{V}$ , $R_L = 50\ \Omega$<br>$I_D \cong 1\ \text{A}$ , $V_{GEN} = 10\ \text{V}$ , $R_G = 6\ \Omega$ |     | 10    | 15        | ns            |
| Rise Time                                     | $t_r$        |                                                                                                                        |     | 15    | 25        |               |
| Turn-Off Delay Time                           | $t_{d(off)}$ |                                                                                                                        |     | 20    | 30        |               |
| Fall Time                                     | $t_f$        |                                                                                                                        |     | 15    | 25        |               |
| Source-Drain Reverse Recovery Time            | $t_{rr}$     | $I_F = 3.2\ \text{A}$ , $di/dt = 100\ \text{A}/\mu\text{s}$                                                            |     | 45    | 90        |               |

## Notes

- a. Pulse test; pulse width  $\leq 300\ \mu\text{s}$ , duty cycle  $\leq 2\%$ .  
b. Guaranteed by design, not subject to production testing.

**TYPICAL CHARACTERISTICS ( $25^\circ\text{C}$  UNLESS NOTED)**

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